Nabiha Ben Sedrine

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Europium-Implanted AlN Nanowires for Red Light-Emitting Diodes. ACS Applied Nano Materials, 2022, 5, 972-984.	2.4	11
2	Enhancing the luminescence yield of Cr3+ in <i>β</i> -Ga2O3 by proton irradiation. Applied Physics Letters, 2022, 120, .	1.5	8
3	Luminescent silver nanoclusters decorated on ZnO tetrapods: a detailed understanding of their role in photoluminescence features. Journal of Materials Chemistry C, 2021, 9, 7014-7026.	2.7	9
4	Eu3+ optical activation engineering in Al Ga1-N nanowires for red solid-state nano-emitters. Applied Materials Today, 2021, 22, 100893.	2.3	4
5	Exploring swift-heavy ion irradiation of InGaN/GaN multiple quantum wells for green-emitters: the use of Raman and photoluminescence to assess the irradiation effects on the optical and structural properties. Journal of Materials Chemistry C, 2021, 9, 8809-8818.	2.7	5
6	Clustering and Morphology Evolution of Gold on Nanostructured Surfaces of Silicon Carbide: Implications for Catalysis and Sensing. ACS Applied Nano Materials, 2021, 4, 1282-1293.	2.4	10
7	Silver nanoparticle array on weakly interacting epitaxial graphene substrate as catalyst for hydrogen evolution reaction under neutral conditions. Applied Physics Letters, 2021, 119, 153902.	1.5	2
8	Interplay between thin silver films and epitaxial graphene. Surface and Coatings Technology, 2020, 381, 125200.	2.2	6
9	ZnAl2O4 decorated Al-doped ZnO tetrapodal 3D networks: microstructure, Raman and detailed temperature dependent photoluminescence analysis. Nanoscale Advances, 2020, 2, 2114-2126.	2.2	15
10	Photoluminescence investigations of ZnO micro/nanostructures. Materials Today Chemistry, 2020, 16, 100243.	1.7	17
11	Iridium(III)porphyrin arrays with tuneable photophysical properties. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2020, 235, 118309.	2.0	4
12	Modelling of Optical Damage in Nanorippled ZnO Produced by Ion Irradiation. Crystals, 2019, 9, 453.	1.0	4
13	Probing surface states in C ₆₀ decorated ZnO microwires: detailed photoluminescence and cathodoluminescence investigations. Nanoscale Advances, 2019, 1, 1516-1526.	2.2	18
14	Eu Activation inβ-Ga2O3MOVPE Thin Films by Ion Implantation. ECS Journal of Solid State Science and Technology, 2019, 8, Q3097-Q3102.	0.9	15
15	Buckminsterfullerene hybridized zinc oxide tetrapods: defects and charge transfer induced optical and electrical response. Nanoscale, 2018, 10, 10050-10062.	2.8	44
16	Optical investigations of europium ion implanted in nitride-based diode structures. Surface and Coatings Technology, 2018, 355, 40-44.	2.2	9
17	Fluctuating potentials in GaAs:Si nanowires: critical reduction of the influence of polytypism on the electronic structure. Nanoscale, 2018, 10, 3697-3708.	2.8	13
18	Shifting Lu2SiO5 crystal to eutectic structure by laser floating zone. Journal of the European Ceramic Society, 2018, 38, 2059-2067.	2.8	13

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19	Multiple optical centers in Eu-implanted AlN nanowires for solid-state lighting applications. Applied Physics Letters, 2018, 113, 201905.	1.5	8
20	Optoelectronic Characterization of ZnO Nanorod Arrays Obtained by Pulse Electrodeposition. Journal of the Electrochemical Society, 2018, 165, D595-D603.	1.3	12
21	Hierarchical Aerographite 3D flexible networks hybridized by InP micro/nanostructures for strain sensor applications. Scientific Reports, 2018, 8, 13880.	1.6	7
22	Eu-Doped AlGaN/GaN Superlattice-Based Diode Structure for Red Lighting: Excitation Mechanisms and Active Sites. ACS Applied Nano Materials, 2018, 1, 3845-3858.	2.4	14
23	Spectroscopic analysis of LYSO:Ce crystals. Spectrochimica Acta - Part A: Molecular and Biomolecular Spectroscopy, 2017, 172, 163-167.	2.0	12
24	Hybridization of Zinc Oxide Tetrapods for Selective Gas Sensing Applications. ACS Applied Materials & Interfaces, 2017, 9, 4084-4099.	4.0	135
25	Nanosensors: Multifunctional Materials: A Case Study of the Effects of Metal Doping on ZnO Tetrapods with Bismuth and Tin Oxides (Adv. Funct. Mater. 6/2017). Advanced Functional Materials, 2017, 27, .	7.8	2
26	Multifunctional Materials: A Case Study of the Effects of Metal Doping on ZnO Tetrapods with Bismuth and Tin Oxides. Advanced Functional Materials, 2017, 27, 1604676.	7.8	140
27	YAG:Dy – Based single white light emitting phosphor produced by solution combustion synthesis. Journal of Luminescence, 2017, 183, 251-258.	1.5	19
28	Structural and optical characterization of Gd_2SiO_5 crystalline fibres obtained by laser floating zone. Optical Materials Express, 2017, 7, 868.	1.6	14
29	Substrate and Mg doping effects in GaAs nanowires. Beilstein Journal of Nanotechnology, 2017, 8, 2126-2138.	1.5	7
30	Spectroscopic analysis of the NIR emission in Tm implanted AlxGa1-xN layers. Journal of Applied Physics, 2016, 120, 081701.	1.1	9
31	Correction to "Spectroscopic Analysis of Eu ³⁺ Implanted and Annealed GaN Layers and Nanowires― Journal of Physical Chemistry C, 2016, 120, 6907-6908.	1.5	5
32	Study of damage formation and annealing of implanted III-nitride semiconductors for optoelectronic devices. Nuclear Instruments & Methods in Physics Research B, 2016, 379, 251-254.	0.6	17
33	Quantum well intermixing and radiation effects in InGaN/GaN multi quantum wells. , 2016, , .		1
34	Luminescence studies on green emitting InGaN/GaN MQWs implanted with nitrogen. Scientific Reports, 2015, 5, 9703.	1.6	19
35	Photoluminescence studies of a perceived white light emission from a monolithic InGaN/GaN quantum well structure. Scientific Reports, 2015, 5, 13739.	1.6	19
	Infrared dielectric functions and optical phonons of wurtzite	<u>(()</u>	

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37	Defect luminescence in oxides nanocrystals grown by laser assisted techniques. , 2015, , .		2
38	Spectroscopic Analysis of Eu ³⁺ Implanted and Annealed GaN Layers and Nanowires. Journal of Physical Chemistry C, 2015, 119, 17954-17964.	1.5	13
39	Structural, optical, electrical and morphological study of transparent p-NiO/n-ZnO heterojunctions grown by PLD. Proceedings of SPIE, 2015, , .	0.8	4
40	Luminescence studies on SnO2 and SnO2:Eu nanocrystals grown by laser assisted flow deposition. Physical Chemistry Chemical Physics, 2015, 17, 13512-13519.	1.3	19
41	Rapid thermal annealing effects on the optical properties of GaAs0.9â^'xNxSb0.1 structures grown by MBE. Materials Science in Semiconductor Processing, 2015, 29, 331-336.	1.9	7
42	Effect of Mg doping on the structural and free-charge carrier properties of InN films. Journal of Applied Physics, 2014, 115, 163504.	1.1	16
43	GaN:Pr ³⁺ nanostructures for red solid state light emission. RSC Advances, 2014, 4, 62869-62877.	1.7	5
44	Infrared to vacuum-ultraviolet ellipsometry and optical Hall-effect study of free-charge carrier parameters in Mg-doped InN. Journal of Applied Physics, 2013, 113, .	1.1	22
45	Bandgap Engineering and Optical Constants of YxAl1-xN Alloys. Japanese Journal of Applied Physics, 2013, 52, 08JM02.	0.8	11
46	Spectroscopic Ellipsometry of AP-MOVPE-Grown GaAs1 â^' x Bi x Dilute Alloys. Springer Series in Materials Science, 2013, , 167-179.	0.4	0
47	Infrared ellipsometry and near-infrared-to-vacuum-ultraviolet ellipsometry study of free-charge carrier properties in In-polar p-type InN. Materials Research Society Symposia Proceedings, 2012, 1396, .	0.1	0
48	Temperature dependent effective mass in AlGaN/GaN high electron mobility transistor structures. Applied Physics Letters, 2012, 101, .	1.5	44
49	Y _x Al _{1â^'x} N thin films. Journal Physics D: Applied Physics, 2012, 45, 422001.	1.3	42
50	Elaboration and characterization of nanocrystalline TiO2 thin films prepared by sol–gel dip-coating. Surface and Coatings Technology, 2011, 206, 243-249.	2.2	53
51	Optical properties of InN/In _{0.73} Ga _{0.27} N multiple quantum wells studied by spectroscopic ellipsometry. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1629-1632.	0.8	1
52	Sol–gel synthesis, characterization and optical properties of mercury-doped TiO2 thin films deposited on ITO glass substrates. Applied Surface Science, 2011, 257, 9103-9109.	3.1	34
53	Annealing temperature effect on the properties of mercury-doped TiO2 films prepared by sol–gel dip-coating technique. Applied Surface Science, 2011, 257, 5529-5534.	3.1	14
54	Optical properties of GaAs0.9-xNxSb0.1 alloy films studied by spectroscopic ellipsometry. Thin Solid Films, 2011, 519, 2838-2842.	0.8	4

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55	Photoluminescence studies of 2DEG confinement in InAs ultrathin layer introduced in GaAs/AlGaAs structure. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 2134-2138.	1.3	14
56	Analyzing ab initio infrared spectra and electronic properties of polyethylenimine water complexes in the solid state. Computational and Theoretical Chemistry, 2010, 945, 27-32.	1.5	11
57	Correlation between microstructure and optical properties of nano-crystalline TiO2 thin films prepared by sol–gel dip coating. Applied Surface Science, 2010, 257, 670-676.	3.1	105
58	Effect of nitrogen on the GaAs0.9â^'xNxSb0.1 dielectric function from the near-infrared to the ultraviolet. Applied Physics Letters, 2010, 97, 201903.	1.5	17
59	Spectroscopic ellipsometry study of GaAs1â ^{°°} xBix material grown on GaAs substrate by atmospheric pressure metal-organic vapor-phase epitaxy. Applied Physics Letters, 2009, 95, 011910.	1.5	14
60	Optical constants and critical-point parameters of GaAs1-xSbxalloy films grown on GaAs. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 833-836.	0.8	2
61	Spectroscopic ellipsometry analysis of GaAs1â^'xNx layers grown by molecular beam epitaxy. Materials Science and Engineering C, 2008, 28, 640-644.	3.8	9
62	Abnormal optical behaviour of InAsSb quantum dots grown on GaAs substrate by molecular beam epitaxy. Materials Science and Engineering C, 2008, 28, 918-922.	3.8	0
63	Observation of many-body Coulomb interaction effects on the photoluminescence spectra of InAs/GaAs quantum dots. Applied Surface Science, 2008, 254, 3125-3129.	3.1	9
64	Optical properties of GaInNAsSb/GaAs/GaAs1â^'xNx (xâ‰^10%) saturable absorber quantum wells. Applied Surface Science, 2008, 254, 7122-7126.	3.1	1
65	Ellipsometric investigation of porous silicon layers for the design of a DBR. EPJ Applied Physics, 2008, 43, 87-91.	0.3	4
66	Strain effects of InP/Si and InP/porous Si studied by spectroscopic ellipsometry. EPJ Applied Physics, 2008, 42, 99-102.	0.3	0
67	Photoluminescence study of the GaAs barrier effect on GaAs/GaInAs/GaAs quantum wells. , 2007, , .		0
68	Optical Constants of As-grown and RTA GaAs1-xNx Layers Analysed by Spectroscopic Ellipsometry. , 2007, , .		0
69	Redistribution of nitrogen localized states in GaAsN layer doped Silicon. EPJ Applied Physics, 2007, 38, 221-225.	0.3	0
70	Deep Defects Annihilation in GaAs1-xNx Layers by Si-doping. American Journal of Applied Sciences, 2007, 4, 19-22.	0.1	6